A key requirement in micro- and nanotechnology device fabrication is the controlled production of layered material components. The semiconductor technology relies on silicon and its native oxide SiO$_2$ as a prime material system due to its simple producibility and outstanding interface properties [1]. Although SiO$_2$ is gradually replaced as a gate dielectric by other materials with much higher dielectric constants [2, 3] – generally referred to as high-$k$ dielectrics – an ultra-thin SiO$_2$ passivation layer that is grown on the Si substrate before the deposition of the high-$k$ film substantially improves the device performance [4–6] and is therefore typically used. In the course of the ongoing down-scaling trend, research interest recently shifts towards low-temperature chemical-based bottom-up fabrication approaches [7–9] in which the production of ultra-thin SiO$_2$ layers is of crucial importance. SiO$_2$ layers are typically fabricated via thermal oxidation of Si. The physical mechanisms of this process have been investigated for decades, both experimentally and theoretically. Today, details of the initial oxidation stage that have not been subject of previous research, which was focused on thicker layers, have become more and more relevant. Problems like the onset of amorphization or the interplay between various oxidation mechanisms are still unresolved.

Among the various theoretical assessments of thermal oxidation, the model developed by Deal and Grove accurately describes the silicon oxidation process [10]. The model follows the well-established concept for Si oxidation that O$_2$ molecules enter the SiO$_2$ surface layers and diffuse to the Si/SiO$_2$ interface where they dissolve and individually relax into their respective lattice sites [11–13]. However, these assumptions seem to be only valid for a well-progressed oxidation stage (oxide thickness $> 30$ Å) as the model predictions strongly underestimate the growth rates for thin oxide films [19, 20]. Previous ab initio calculations showed that the initial oxidation of a clean Si surface is based on chemisorption events resulting in the dissociation of the adsorbing O$_2$ molecule directly at the surface [21, 23]. This was confirmed experimentally in recent electron microscopy and photoemission studies [24–26]. In addition to directly dissociative O$_2$ adsorption, metastable molecular surface states were observed by means of scanning electron microscopy (SEM) and electron spectroscopy techniques on thin oxide layers [25, 26]. These molecular states precede dissociation at low temperatures and vanish upon annealing. Hence, the dissociated O$_2$ molecule provides a more stable configuration and the molecular states are solely intermediate states of the dissociative surface reaction. Both, direct dissociation upon adsorption as well as molecular O$_2$ precursors that subsequently dissociated...
were observed in molecular beam experiments [31]. According to this study, incident O\textsubscript{2} molecules of high kinetic energy (> 1 eV) tend to dissociate directly, whereas the molecular precursor states originate from trapping-mediated adsorption of O\textsubscript{2} with low kinetic energy (< 0.2 eV). Upon dissociation, the O atoms moved into backbonds of Si surface atoms, as correctly predicted by the above mentioned theoretical studies [21]–[23].

Combining these results, two major kinetic mechanisms seem to be at work: surface reactions dominate the initial stage, while the diffusion of O\textsubscript{2} becomes more important as the oxidation continues. Based on this concept, a theoretical growth model that considered dissociative chemisorption at the surface has been formulated [32] and reported to give good agreement with experimental data. The existence of two oxidation stages was also observed experimentally. As reported in a photoelectron spectroscopy study [33], the initial stage at low O\textsubscript{2} exposure of up to 10 L (1 L: 10\textsuperscript{-6} Torr s) featured relatively rapid oxidation. Maintaining the supply of O\textsubscript{2}, the oxygen surface coverage saturated and the oxidation rate was reduced as the system gradually transitioned into the Deal-Grove regime. According to transmission electron microscopy (TEM) experiments on Si nanoparticles, diffusion of O\textsubscript{2} molecules becomes important after formation of a 5 Å thick oxide layer [24].

The onset and origin of amorphization of the oxide layer is still a controversial issue in literature. Although some studies predicted crystalline Si oxide monolayers [34]–[35], an increase in the surface roughness during the initial oxidation was observed by atomic force microscope measurements [20] indicating an amorphous oxide growth. More recent TEM measurements supported this idea and reported evidence that amorphous oxides were obtained by rapid thermal oxidation (RTO) [24]–[36]. However, only oxide layers with thicknesses of more than 10 Å, corresponding to roughly four oxidized Si layers, were studied, whereas our simulations offer detailed insight into the oxidation process from the onset of oxidation.

In this work the initial stage of thermal oxidation of Si at \( T = 1000\,\text{K} \) was studied up to an oxide thickness of 20 Å in order to investigate the growth and amorphization of ultra-thin Si oxide layers. Preliminary data regarding this topic was already published in our recent work [37]. However, the present work provides a detailed and complete study, beyond the results shown in [37], on the thermal oxidation and its intricacies associated with its various stages. For the first time, the growth of an ultra-thin SiO\textsubscript{2} layer was realistically modeled within dynamic simulations that allowed confirmation and unification of all experimental and theoretical knowledge that has been gained on this subject until now. The oxidation process was realistically modeled by the subsequent adsorption of O\textsubscript{2} molecules within \textit{ab initio} molecular dynamics (AIMD) simulations in conjunction with density functional theory (DFT). In addition, energy barriers for the migration of oxygen in the oxide layers were obtained by nudged elastic band (NEB) calculations. The initial oxidation process featured the fastest oxidation rate enabled by spontaneous surface reactions which include the dissociation of chemisorbing O\textsubscript{2} molecules. An immediate amorphization was indicated by arbitrarily incorporated oxygen along many possible adsorption trajectories that led to the spontaneous formation of SiO\textsubscript{4} tetrahedrons, the characteristic structural elements of a-SiO\textsubscript{2}. With increasing O coverage, we observed that O-coordinated Si atoms were less susceptible for O\textsubscript{2} chemisorptions. Hence, repulsion of the incident O\textsubscript{2} became more probable and the oxidation rate decreased gradually as the surface is oxidized. In this stage, immediate dissociation (< 0.5 ps) was only enabled for O\textsubscript{2} molecules of high kinetic energy and the more likely molecular precursor states that dissociated after a few ps were observed for slower oxygen molecules leading to a further decrease in the oxidation rate. The migration of O\textsubscript{2} molecules through the oxide was investigated on a 20 Å thick surface layer of a-SiO\textsubscript{2}. Diffusion of O\textsubscript{2} set in as soon as a sufficiently thick surface layer was saturated with O. The saturation was consistent with the formation of a-SiO\textsubscript{2} and indicated the transition into the Deal-Grove regime. A spontaneous dissociation via the same charge transfer process responsible for the surface dissociation was then observed at the Si/SiO\textsubscript{2} interface.

**METHODOLOGY**

Our calculations were mainly conducted at the \textit{ab initio} level utilizing density functional theory (DFT). In order to study oxidation mechanisms beyond the initial steps of O adsorption and dissociation, further investigations inevitably had to be carried out on larger model systems. Especially for DFT calculations, the computationally feasible system size was limited to a few hundred atoms and could be even lower for structures with an increased density of crystallographic defects. In order to enrich our data set in a computationally feasible manner, we additionally used density functional based tight binding (DFTB) in conjunction with a Slater-Koster parameter set designed for Si surfaces and interfaces with SiO\textsubscript{2} [38]–[39]. Initial benchmarks showed that both methods yield comparable results. The details of the utilized methods and their applications within this work are summarized below.

**DFT setup**

All density functional theory calculations were carried out using the CP2K package [40], a code that uses the mixed Gaussian and plane waves approach (GPW).
We used a double-ζ Gaussian basis set that was optimized for condensed-phase systems consisting of Si, O, and H and the well-established Goedecker-Teter-Hutter (GTH) pseudopotentials [41,42]. The electron density was expanded using a plane-wave basis with a cutoff of 650 Ry. The exchange-correlation energy was obtained by means of the semilocal generalized gradient approximation (GGA) functional PBE. Due to its efficiency, the orbital transformation (OT) method was used by default to find the ground-state electronic structure [43]. However, within dynamic AIMD calculations, where several O atoms and potentially multiple unsaturated bonds were involved, Broyden’s method proved to be more stable and was used instead [44]. Atomic relaxations were carried out using the Broyden-Fletcher-Goldfarb-Shanno (BFGS) algorithm [45] with a force convergence criterion of 15 meV/Å. Within the AIMD simulations, the total energy was conserved (microcanonical or NVE ensemble) and the total spin was restricted to $S = 0$. The minimal energy barrier between two configurations was calculated using the climbing-image NEB (CI-NEB) method [46,47] with a spring constant of $k = 8.2$ eV/Å$^2$.

DFTB setup

The DFTB method uses an expansion of the total energy of DFT with respect to the charge density [48]. Hamiltonian matrix elements and overlap integrals are approximated by interpolations between two-atom calculations obtained from DFT. These approximations reduce the computational costs drastically. Our DFTB simulations were carried out using the DFTB+ package [48], employing the Slater-Koster parameter set pbc-0-3 [59], which is suitable for solids and surfaces of Si-O-H systems. We considered atomic basis functions up to the s-, p- and d-shells for H, O, and Si, respectively. For geometry optimizations again the BFGS algorithm implemented in the DFTB+ package was utilized. The DFTB approach as well as the pbc-0-3 parameter set [59] are well justified as reported by a number of previous studies [49,51]. The agreement between AIMD and DFTB calculations within the framework of the present paper was ensured by a number of test calculations, e.g., the adsorption of O$_2$ molecules showed the same charge transfer of $-e$ as well as comparable reaction kinetics and adsorption configurations. Furthermore, recalculation of an AIMD trajectory yielded comparable energy gains as well. The comparative calculations are given in the supplementary material.

Preparation of atomic structures

The starting point of our investigations was a $4 \times 4 \times 12$ reconstructed Si surface structure. A cleaved Si surface leads to undercoordinated Si atoms at the surface that reconstruct by forming alternating rows of tilted dimers to minimize its energy. This reconstruction reduces the number of dangling bonds on the surface via electron transfer from the lower Si dimer atom to the upper one [52]. In the present structure eight dimer pairs formed within the simulation cell. The dimers were aligned in rows that build terraces on the surface separated by cavities, so-called channels. The dangling bonds at the bottom of the structure were passivated with hydrogen. The bottom Si layer and the passivating H atoms were fixed in AIMD runs to resemble a bulk like structure. After reconstruction of the surface, optimizing the cell including the ionic cores in the lateral directions within DFT resulted in cell dimensions of $a = b = 15.523$ Å. The cell size in the c-direction was set to $c = 37.22$ Å leaving a vacuum of 20 Å above the slab. The thermal oxidation of Si was studied on this model by means of AIMD until 1.1 ML of O were adsorbed. Thereafter, we employed DFTB to model the thermal oxidation up to an oxide thickness of 8.5 Å. Investigations of O$_2$ migration through the oxide were carried out on a thicker oxide model which was obtained by a melt and quench procedure [53–57] using classical molecular dynamics. Details of this procedure are given in Ref. [53]. Subsequently, this model was relaxed within DFT and passivated with H. Finally, the resulting surface was relaxed again. The finished surface model consisted of a $3 \times 3 \times 12$ Si substrate with roughly 20 Å of SiO$_2$ on top, adding up to a total of 290 atoms.

RESULTS AND DISCUSSION

A detailed picture of oxygen incorporation and amorphization at the initial stage of thermal oxidation of Si could be established from the outcome of our simulations. Our results explain the experimentally observed transition from a fast to a slow oxidation regime [24,53] by various oxygen incorporation mechanisms that supersede each other during the oxidation of only a few layers of Si. The key findings presented in this section are:

- Spontaneous surface reactions upon which the involved O$_2$ molecules dissociated.
- Immediate amorphization of the oxide layer.
- Molecular precursor states provided for a slower oxidation rate in a more progressed stage of oxidation.
- Oxygen surface saturation marked the beginning of O$_2$ diffusion through the oxide.
- Dissociation at the Si/SiO$_2$ interface due to the same charge transfer process that characterized the
initial surface reactions.

Dynamic simulations of thermal surface oxidation

Thermal oxidation, i.e. oxidation at temperatures in the range of 1000 K, was realistically modeled by dynamic simulations in which O$_2$ molecules adsorbed to the Si surface. Optimizing structures within static calculations led to crystalline oxide monolayers as presented in the supplementary material. However, including dynamics into our simulations clearly showed that the respective adsorption trajectory strongly depends on the initial position and velocity of the incident O$_2$ molecule and surface atoms. This results in a stochastic adsorption process which ultimately prevents the growth of an ordered oxide under realistic conditions of thermal oxidation. Our investigations on the DFT level started from the Si(100) surface with a $p(2 \times 2)$ reconstruction and ranged up to the adsorption of 13 O$_2$ molecules, corresponding to a coverage of 1.6 ML (1 ML: 6.78 × 10$^{14}$ atoms/cm$^2$) in our structures, offering insight into the amorphization of the first oxide layer. In order to study the further progression of oxidation, we employed DFTB in the following until a 8.5 Å thick oxide layer was obtained.

O$_2$ adsorption onto the clean Si surface

Our investigations started with a single O$_2$ molecule that was placed 2.5 Å above the reconstructed Si(100) surface. An ensemble of randomly generated and normally distributed velocities, scaled to match the specified temperature $T = 1000$ K, was assigned to the atoms and a spin-restricted ($S = 0$) AIMD simulation with a simulation time of 1 ps and a step size of 0.5 fs was performed. Subsequently, the structure was relaxed within DFT. In this vein, we conducted several simulations with various starting configurations that yielded consistent results. Fig. 1 shows snapshots of one representative O$_2$ adsorption and dissociation event together with the associated charges obtained by a Mulliken charge analysis of the oxygen molecule and its neighboring Si atoms. The O$_2$ molecule spontaneously moved toward an upper Si dimer atom that was charged positively as the O$_2$ molecule approached. After 170 fs the molecule was centered above the Si dimer atom and started to dissociate. Within the next 80 fs, the dissociation process was completed and the charges remained constant for the rest of the simulation. The two oxygen atoms relaxed into the backbonds of the upper Si dimer. In total, a charge of roughly $0.7 e$ was transferred from the surrounding Si surface atoms to the O$_2$ molecule. In a simple molecular orbital picture, the donated electron occupied the antibonding $\pi^*$ orbital of the O$_2$ molecule, triggering its dissociation. Note that the gradual increase of charge depicted in Fig. 1 resulted from the adiabatic representation within DFT. In reality, the charge would be transferred much faster in a non-adiabatic process. Regardless, a spontaneous dissociative surface reaction was indicated by the very rapid reaction with the Si surface that was found to be independent from the starting configuration. This result was further supported by a series of static calculations. Placing O$_2$ molecules at random positions above the clean and reconfigured Si(100) surface and relaxing the structure within DFT led to the dissociation of the molecule. Furthermore, a barrierless dissociative oxidation was also reported in [22]. Compared to the pre-adsorbed state, the intact O$_2$ molecule above the pristine Si slab, the dissociated and geometry optimized structure was 7.28 eV lower in energy. As shown in the last snapshot in Fig. 1, the Si atom on top was still undercoordinated yielding a surface dangling bond. This exact configuration was already observed experimentally by STM images of a sparsely oxidized Si surface [26].

![Fig. 1. The dissociative chemisorption of O$_2$ (red atoms) onto a clean and reconstructed Si(100) surface (yellow atoms). Snapshots of the AIMD simulation are given in the upper panel. The top right panel shows the geometry optimized structure after dissociation. The spin density for values $\pm 0.002 e/\text{a}_0^3$ is depicted by cyan and magenta isosurfaces, respectively. The Mulliken charges of the oxygen atoms, the top dimer Si atom (T), and the neighboring Si atoms (N) during the first 500 fs of the chemisorption are shown in the lower left panel. A barrierless adsorption and dissociation is indicated by a NEB calculation along the adsorption trajectory in the lower right panel.](image)

Initial amorphization

Crystalline oxide structures on Si surfaces have been investigated thoroughly within theoretical studies [34] and also within the framework of this work, see supplementary material. However, the fact that thermally...
grown SiO$_2$ is amorphous was established decades ago and more recent studies reported evidence that this is also true for thin films of 10 Å to 50 Å obtained by RTO, as reported by various TEM studies [24, 36]. However, it is still unclear if the very first oxide layer is already amorphous. Within our dynamic simulations, strong evidence for immediate amorphization was found as presented in the following.

We modeled the thermal oxidation process by a series of AIMD simulations at 1000 K in which O$_2$ molecules were consecutively introduced above the reconfigured Si(100) surface as shown in Fig. 1. The individual initial position was assigned randomly within a distance of 2 Å to 3 Å above the top Si atom. The axis of the O$_2$ molecule was aligned with the surface in order to allow for effective interaction due to larger spatial overlap between the surface dangling bonds and the oxygen π* orbital. The simulation time for each adsorption event was set to 1 ps. After this time, another O$_2$ molecule was introduced similarly to the previous one, while all other atoms continued to move according to their current velocity. A Mulliken charge analysis showed that the fundamental oxidation mechanism – a dissociative chemisorption via a charge transfer similar to the reaction shown in Fig. 1 – underlay every single adsorption during the initial surface oxidation. However, adsorption became less probable as the oxidation progressed. Only the first six adsorptions, corresponding to an oxygen coverage of 0.7 ML in our structures, happened spontaneously. After that, the O$_2$ molecules were occasionally repelled from already oxidized Si atoms. In this case, the run was discarded. After 9 successful adsorptions (or 1.1 ML), a spontaneous adsorption could not be observed within 10 runs. We interpreted the decrease in adsorption probability as the emergence and subsequent enhancement of an adsorption barrier with proceeding oxidation. In order to overcome the formed adsorption barrier and to study further oxidation within a reasonable time frame, we imposed an initial velocity of 1000 m/s towards the surface for the O$_2$ molecule from this point onwards. This value roughly complied with the average velocity of $\tau = 810$ m/s according to the Maxwell-Boltzmann distribution of non interacting O$_2$ molecules at $T = 1000$ K. Adsorption of O$_2$ – a process that happened spontaneously onto the clean surface within static and dynamic calculations – was inhibited by the oxide formation on the surface. This behavior qualitatively explained the decrease of the oxidation rate measured in the initial stage of oxidation [33] and gave rise to the non-reactive O$_2$ diffusion process later on [10].

The immediate amorphization of the oxide layer was enabled by a stochastic adsorption process in which the adsorption trajectory of each O$_2$ molecule depended strongly on its initial position and velocity and even on fluctuations of the surface lattice due to thermal vibrations. The stochastic character of the oxidation process was indicated by many different adsorption trajectories featuring comparable energy gains and strongly varying final configurations. Representative adsorption trajectories of three successive runs are given in the supplementary material.

The adsorption trajectories were very sensitive to changes of the environment as investigated by two comparative AIMD runs. As shown in Fig. 2 the adsorption of an O$_2$ molecule was sampled for two different velocity distributions (taken from a Maxwell-Boltzmann distribution as described above) of the surface lattice. The initial position and velocity of the O$_2$ was identical for both runs. The resulting trajectories are completely different although the energy gain of around 6.5 eV is very similar. This implies that even weak perturbations alter the resulting structure substantially. Furthermore, the high degree of randomness in the oxidation process is a strong evidence for the immediate amorphization of the oxide layer.

\[ \Delta E = 6.29 \text{ eV} \]

\[ \Delta E = 6.72 \text{ eV} \]

FIG. 2. Comparative trajectories of O$_2$ adsorptions with the same initial position and velocity of the O$_2$ molecule but different velocities for the surface atoms. The velocities of the lattice atoms were randomly sampled from a Maxwell-Boltzmann distribution at 1000 K. The snapshots show the atomistic configuration after a simulation time of 450 fs. Additionally depicted are the starting position of the oxygen molecules together with the trajectories of the adsorbing O atoms (red lines). The energy gains $\Delta E$ were calculated for geometry optimized structures.
Molecular precursors

In order to sample slower surface reactions and more spontaneous adsorptions that are not affected by artificial initial velocities, the simulation time as well as the number of runs needed to be increased. Furthermore, extending our investigations in the direction of the formation of a-SiO$_2$ required a larger amount of oxygen. Hence, we conducted these calculations within DFTB. The molecules were placed about 2 to 3 Å above a surface Si atom before MD simulations of 10 ps with a step size of 0.5 fs were conducted. The first simulation started with random initial velocities for all atoms that were passed on to the subsequent run. As for the previous AIMD calculations we imposed an initial O$_2$ velocity in negative z-direction, however, here a velocity was randomly sampled from a thermal velocity distribution (Maxwell-Boltzmann) ranging from 50 m/s to 1000 m/s to realistically reflect the temperature of the O$_2$ atmosphere. If a molecule was repelled from the surface, it was removed from the simulation cell at the end of the run. After the first Si layer was oxidized, spontaneous dissociative adsorptions could hardly be observed. Instead, the O$_2$ molecules adsorbed to a already fully oxidized Si atom (the SiO$_4$ tetrahedron is indicated by blue planes) and stays in the vicinity of this atom for around 4 ps within our simulations. Finally, the oxygen molecule dissolves. Two O atoms migrate to lower Si atoms in order to adjust for the incorporation of the dissolved O atoms, as indicated by the black arrows.

![Molecular precursor states](image)

**FIG. 3.** Molecular precursor states. The O$_2$ molecule adsorbs to a already fully oxidized Si atom (the SiO$_4$ tetrahedron is indicated by blue planes) and stays in the vicinity of this atom for around 4 ps within our simulations. Finally, the oxygen molecule dissolves. Two O atoms migrate to lower Si atoms in order to adjust for the incorporation of the dissolved O atoms, as indicated by the black arrows.

The oxide layer reached a total thickness of 8.5 Å after the adsorption of 32 O$_2$ molecules or 4 ML. As presented in the following section, the oxide could be subdivided into a 3.5 Å thick layer of a-SiO$_2$ on top of a 5 Å transition region. In this stage, all Si atoms on the surface were fully O coordinated and incorporated in a spontaneously formed SiO$_4$ tetrahedron, see Fig. 3 and 4. As a result, the surface structure was highly unorderd. A spontaneous adsorption of O$_2$ molecules onto this surface could not be observed, as an additional molecule was repelled from 25 random positions. The chemical composition of the a-SiO$_2$ surface layer was SiO$_{1.95}$. A structural analysis of this layer showed that the bond lengths and angles are already comparable to the experimentally obtained values for bulk a-SiO$_2$ [58, 59]. The average Si-O distance was 1.66 Å and the binding angles showed an average of 108° for O-Si-O and 132.5° for Si-O-Si, see Fig 4. The slightly larger bond lengths (compared to 1.62 Å of bulk SiO$_2$) could be assigned to surface effects. The O-Si-O angles matched the perfect tetrahedral bond angle of 109.47°. The Si–O–Si angle averaged at 132.5°, which agreed well with the conclusions reached in Ref. [60], that the angle is reduced to 135° in thin films compared to 148° in bulk structures. Furthermore, the Si-O-Si angles were broadly distributed between 100° to 160° which indicated a vitreous (amorphous) form of silica. The density of the SiO$_2$ layer was roughly 2.33 g/cm$^3$ in agreement with measured values [58]. The density of the transition layer directly at the Si/SiO$_2$ interface was slightly increased to values up to 2.8 g/cm$^3$ which complied with an intrinsic compressive stress as reported in Ref. [61, 62]. A Mulliken charge analysis allowed to infer the oxidation state of each Si. Due to the strong electronegativity of O, a Si-O bond was reflected by an increase of the Si’s associated Mulliken charge. As determined by a reference calculation in defect-free a-SiO$_2$, the fully oxidized state Si$^{4+}$ corresponded to an increase of roughly 1e in our DFT setup, yielding ~0.25e of excess charge on the Si ion per Si-O bond. The prevalence of different Si oxidation states as determined by this relation during the thermal oxidation is shown in the middle panel in Fig. 4. For a sparsely oxidized surface, the O was distributed evenly on the Si atoms as shown by the large number of Si$^+$. In later stages however, most Si were fully O coordinated with only a few partially O-coordinated Si atoms that were located at the interface to the Si substrate. Si$^{4+}$ atoms were fully coordinated by O and incorporated in a SiO$_4$ tetrahedron. We observed that the transition into the O$_2$ diffusion regime (Deal-Grove regime) hap-
FIG. 4. Characteristics of the SiO$_2$ growth obtained by dynamic simulations within DFTB. Distributions of the bond lengths and angles and the comparison to experimental values of bulk SiO$_2$ [58, 59] (dashed lines) are shown in the top panel. The prevalence of different Si oxidation states as obtained by a Mulliken charge analysis is shown in the middle panel. As oxidation continues, the amount of Si$^{4+}$ (fully oxidized Si atoms that are incorporated in SiO$_4$ tetrahedrons) increases whereas the amount of Si$^+$ converges to a lower value that represents states in the transition region (TR) between the oxide and the crystalline Si substrate. The final and geometry optimized structure is shown in the lower panel. SiO$_4$ tetrahedrons on the immediate surface are indicated by blue planes.

pened as soon as a sufficiently thick surface layer was fully oxidized. In this stage, the O$_2$ could not chemically react with the surface anymore and thus diffusion of O$_2$ through the oxide set in.

**Si/SiO$_2$ interface**

Within computational material modeling, the construction of credible interface structures between amorphous oxides and crystalline substrates is a challenging task [63, 64]. Typically, computationally modeled Si/SiO$_2$ interfaces are created using a melt and quench procedure [53, 54]. In this approach, atomistic structures are melted at temperatures of up to 7000 K within simulation times of tens of picoseconds while keeping directly adjacent regions frozen. In contrast, by consecutively adsorbing O$_2$ molecules onto the Si surface in dynamic simulations, we naturally obtained a credible interface between the amorphous oxide and the crystalline Si substrate. In order to investigate oxidation states at the interface, we plotted the Mulliken charges of the Si atoms vs. the corresponding z-position, as shown in Fig. 5. Note that the oxidation state +1 that is associated with one Si-O bond corresponded to a charge transfer of 0.25e in the Mulliken charge analysis. In addition to our observations, previous studies reported an intrinsic stress around the interface [61, 62]. This stress gave rise to lattice distortions that blurred the Mulliken charge analysis. Hence, only a rough assignment of oxidation states in the transition region was attainable. The decrease of the charge of some Si atoms in the transition region was considered to be an artifact of lattice distortions, as these atoms were situated in a layer below the oxidation front and correctly coordinated to other Si atoms. However, bonding lengths to upper Si atoms were stretched by about 4% or 0.1 Å which directly affects the Mulliken charge. In the following section, we show that these weakened interface bonds represented preferred places for the dissociation of O$_2$ molecules. All Si atoms in the surface SiO$_2$ layer were fully oxidized and their associated Mulliken charge was increased by e. The transition region was about 5 Å thick and could be identified via intermediate charge states of the silicon atoms. The linear transition of associated charges in the transition region was also found in structures obtained by the melt and quench method [53]. Furthermore, interface regions between crystalline Si and the amorphous oxide of 5 Å to 7 Å were indicated by TEM images [58] and electron-energy-loss spectroscopy (EELS) measurements.

**Oxygen migration**

Another important aspect of the surface oxidation process is the migration of incorporated oxygen. First, we examined the possibilities of thermal diffusion of single O atoms by calculating energy barriers for the migration in Si bulk and from the surface oxide into deeper layers of the Si surface. Subsequently, the diffusion of O$_2$ molecules through the amorphous oxide layer was investigated by dynamic simulations showing that O$_2$ is non-reactively incorporated into the oxide and spontaneously dissolves at the Si/SiO$_2$ interface.
Migration of adsorbed O atoms

To have an upper limit of single O atom migration in a bulk Si system we first calculated the energy barrier for the migration of one single O atom in a Si bulk material. As verified within geometry optimizations, the energetically favored positions of an O atom incorporated in a Si crystal are the Si bond center sites [66]. Utilizing NEB calculations, we obtained the minimum energy path between two neighboring bond center sites. The energy barrier of 1.72 eV in our pristine Si crystal complies with other theoretical studies of O migration in Si [67–69]. With this result the experimentally derived energy barrier of 2.53 eV [70] can be obtained by considering a coupled-barrier diffusion [71]. In order to derive an estimate for the rate of the process at $T = 1000$ K we employed the Arrhenius equation with an attempt frequency of $6 \times 10^{12}$ s$^{-1}$ [72] and the 1.72 eV barrier yielding $9 \times 10^4$ s$^{-1}$. Enlarged barriers were found for O migration from the surface oxide structures obtained by our AIMD simulations, see Fig. 6. We specifically investigated diffusion in the transition region between the crystalline and amorphous structures since it offered alternative positions for O atoms. Two examples of possible diffusion paths for one O atom were calculated and yielded energy barriers of at least 2.8 eV, or a reaction rate of $40 \times 10^{-3}$ s$^{-1}$. Keeping the oxidation growth rate of about 1 A/s [73] for the initial stage of thermal oxidation of Si in mind, only a small contribution to the overall growth rate by thermal O migration is expected. Note that the energy barriers were obtained within a static approximation at 0 K but should be valid for moderate temperatures as well.

O$_2$ diffusion through the oxide

Diffusion of O$_2$ through thicker oxide layers during thermal oxidation as proposed by [10] was well investigated in other studies [11–18, 74–76]. The diffusion barrier was found to be extremely sensitive to the local structural topology which is reflected by a wide spread of DFT calculated values from 0.5 eV to 2.8 eV [13, 74]. Experimentally, values between 0.7 and 1.6 eV [76] were found for oxide films produced in various ways. We verified the validity of our structures and computational methods by NEB calculations of O$_2$ diffusion processes in a-SiO$_2$ along trajectories with distances between 5 and 8 Å that yielded barriers between 0.7 and 2 eV. Hence, molecular stability as well as sufficient diffusibility of O$_2$ in silicon dioxide can be safely assumed also within the framework of our calculations. We observed the non-reactive adsorption of O$_2$ molecules on a 20 Å thick oxide layer that was obtained by a melt and quench procedure [53]. As shown in Fig. 7 a seamless migration through the oxide could be sampled in an AIMD simulation with a simulation time of 1 ps. The molecules‘ initial velocity was set to 1000 m/s. Without interaction the O$_2$ entered
FIG. 7. The diffusion of $O_2$ in a-SiO$_2$ is enabled for thicker oxide layers. The non-reactive incorporation and migration through the oxide layer is shown by the results of an AIMD simulation with a simulation time of 1 ps. The trajectory of the center of mass (COM) of the molecule is depicted by a solid blue line. For longer simulation times, the molecule would eventually reach the Si/SiO$_2$ interface.

In the $O_2$ diffusion regime, further oxidation of the Si substrate happens at the Si/SiO$_2$ interface upon dissociation of the $O_2$ molecule [10] as could be confirmed within our simulations by another set of AIMD calculations.

An $O_2$ molecule was placed in the transition region between the amorphous oxide and its crystalline substrate. Due to lattice distortions, some Si atoms in the transition region possess strained bonds or even dangling bonds, cf. Fig. 5. These dangling bonds are known to affect the reliability of semiconductor devices and are therefore usually passivated with H after the oxidation [53, 77]. However, the simulations showed that these atoms offered the preferred dissociation spots. The initial velocity of the $O_2$ was set to zero in order to verify the feasibility of a spontaneous reaction. As shown in Fig. 5, the $O_2$ molecule spontaneously dissolved via essentially the same charge transfer process as in the dissociative chemisorption at the Si surface, cf. Fig. 1. In addition, further evidence for a barrierless dissociation was obtained by another NEB calculation. Here, the $O_2$ was placed above the transition region in order to include a short diffusion path of 4 Å preceding to the actual dissociation. The migration towards the strained bond was governed by a comparably low diffusion barrier of 0.2 eV.

In Fig. 8, the beginning of the dissociative process is indicated by a strong decrease of the potential energy surface. The large energy gain of 9.4 eV could be justified by a complex reconfiguration at the interface in which multiple bonds with considerable binding energies break ($O-O$: 2.1 eV; Si-Si: 4.9 eV) and form (Si-O: 6.5 eV). Additionally, the molecular configuration contained the incorporation energy of the oxygen molecule in the oxide layer which was evaluated to be 0.4 eV in bulk SiO$_2$ by DFT calculations [78]. In this stage, the oxide growth rate is not limited by the supply of oxygen to the surface anymore but by the $O_2$ diffusion rate through the oxide and is thus certainly much slower compared to the initial oxidation, as assumed within the Deal-Grove model [10].

CONCLUSION

We modeled the oxidation of a Si(100) surface by means of ab initio DFT and the closely related DFTB simulation techniques and obtained credible surface models of ultra thin native oxide layers on a Si substrate. For the first time, simulations of the highly complex thermal oxidation process could reproduce all experimental observations that have been reported up to now. By doing so, a complete picture of the whole process with its various mechanisms can be sketched.

Starting from the clean $p(2 \times 2)$ reconstructed Si surface we gradually introduced molecular oxygen into the system by adding $O_2$ molecules above the surface and dynamically modeled their chemisorption until a 3.5 Å thick SiO$_2$ layer formed above a 5 Å transition region. Immediate amorphization from the onset of oxidation was indicated by a stochastic adsorption processes in which many barrierless adsorption trajectories with similar energy gains of around 6 eV led to strongly varying final positions. The top a-SiO$_2$ layer showed many characteristics of bulk SiO$_2$ such as geometric measures (bond angles and lengths) and density already for thicknesses of $\sim 3.5$ Å. Furthermore, it consisted of SiO$_4$ tetrahe-
associated charges of the Si during the initial stage of oxidation, cf. Fig. 1. The Mulliken analysis reveals another charge transfer within an AIMD simulation are depicted in the top right panel. The Mulliken charges for the spontaneous dissociation as captured by a thick transition layer with a substantial amount of strained configurations, it again spontaneously dissolved via a charge transfer reaction that strongly resembled the surface reactions during the initial stage of oxidation.

Based on the qualitative behavior of the oxidation process, estimates for the transition into the diffusive Deal-Grove regime can be given. Direct surface reactions dominate only during oxidation of the first and second Si layer (oxide thickness $\sim$4 Å). Subsequently, in an intermediate stage, molecular precursor states provide for a slower oxidation until a layer of $a$-SiO$_2$ has formed above the $\sim$5 Å transition region. Starting from 10 Å total oxide thickness, the surface should be inert to any surface reactions and thus allow for the diffusion of molecular oxygen.

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FIG. 8. $O_2$ dissociation at the Si/SiO$_2$ interface. The left panel shows the trajectory of the COM of the $O_2$ molecule (solid blue line) together with the initial (molecular) and final (dissociated) configurations of the NEB calculation. The Mulliken charges for the spontaneous dissociation as captured after oxidation of the first Si layer, the molecules were occasionally repelled and direct dissociation could only be observed for molecules with kinetic energies from the top percent of the Maxwell-Boltzmann distribution. However, the adsorption of $O_2$ molecules that only dissociated after some picoseconds (so-called metastable molecular precursor states) was commonly monitored in longer MD runs. The slower dissociation mechanism and the decreased adsorption probability led to an overall decrease of the oxide growth rate in this stage. Finally, the oxide layer became thick enough to effectively block any surface reactions leading to the dissociation of the $O_2$ molecule. Now the diffusion of $O_2$ through the oxide to the Si/SiO$_2$ interface – as assumed within the Deal-Grove model – set in. As soon as the $O_2$ molecule reached the Si/SiO$_2$ transition layer with a substantial amount of strained configurations, it again spontaneously dissolved via a charge transfer reaction that strongly resembled the surface reactions during the initial stage of oxidation.

In the initial oxidation stage, the adsorption of $O_2$ was a spontaneous process and directly followed by the dissociation of the molecule upon which the O atoms moved into Si-Si bond center sites. Thus, this stage features the fastest oxidation rate that is only limited by the supply of oxygen. Further oxidation of a Si surface atom that was already bound to other O atoms was found to require overcoming of an adsorption barrier. Therefore, after oxidation of the first Si layer, the molecules were occasionally repelled and direct dissociation could only be observed for molecules with kinetic energies from the top

percent of the Maxwell-Boltzmann distribution. However, the adsorption of $O_2$ molecules that only dissociated after some picoseconds (so-called metastable molecular precursor states) was commonly monitored in longer MD runs. The slower dissociation mechanism and the decreased adsorption probability led to an overall decrease of the oxide growth rate in this stage. Finally, the oxide layer became thick enough to effectively block any surface reactions leading to the dissociation of the $O_2$ molecule. Now the diffusion of $O_2$ through the oxide to the Si/SiO$_2$ interface – as assumed within the Deal-Grove model – set in. As soon as the $O_2$ molecule reached the Si/SiO$_2$ transition layer with a substantial amount of strained configurations, it again spontaneously dissolved via a charge transfer reaction that strongly resembled the surface reactions during the initial stage of oxidation.

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